# NSN 5962-01-255-0369

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# Body Length:

1.060 inches

# Body Width:

Between 0.220 inches and 0.310 inches

# **Body Height:**

Between 0.130 inches and 0.185 inches

# **Maximum Power Dissipation Rating:**

100.0 milliwatts

#### **Operating Tempurature Range:**

-55.0/+125.0 degrees celsius

#### Storage Tempurature Range:

-65.0/+150.0 degrees celsius

#### **Features Provided:**

Monolithic and programmed and bipolar

#### **Inclosure Material:**

Ceramic

# Inclosure Configuration:

Dual-in-line

#### **Output Logic Form:**

Transistor-transistor logic

## Input Circuit Pattern:

10 input

### Case Outline Source And Designator:

D-8 mil-m-38510

### **Current Rating Per Characteristic:**

90.00 milliamperes reverse current, dc absolute

### **Terminal Surface Treatment:**

Solder

#### **Product Name:**

And-or invert gate array

### Voltage Rating And Type Per Characteristic:

-0.5 volts power source and 12.0 volts power source

### Time Rating Per Chacteristic:

45.00 nanoseconds propagation delay time, high to low level output and 45.00 nanoseconds propagation delay time, low to high level output

#### Memory Device Type:

Pal

### **Test Data Document:**

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

### **Terminal Type And Quantity:**

20 printed circuit

#### Shelf Life:

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Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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